

MA556

Silicon epitaxial planer type

For UHF and SHF bands AGC

■ Features

- Small diode capacity C_D
- Large variable range of forward dynamic resistance r_f
- Mini package, enabling down-sizing of the equipment and automatic insertion through taping and magazine package

■ Absolute Maximum Ratings (Ta= 25°C)

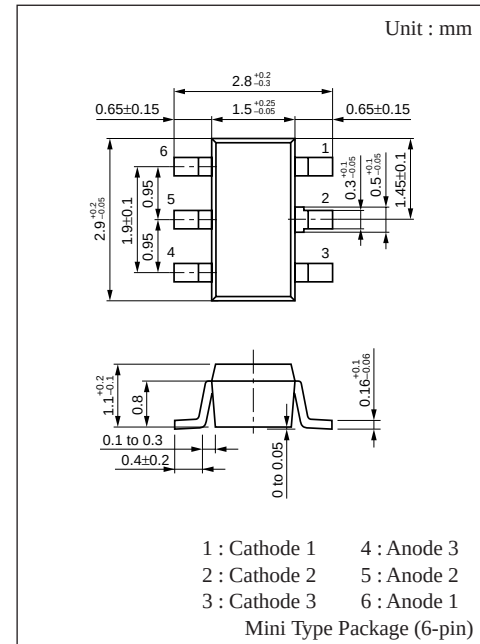
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	40	V
Peak reverse voltage	V_{RM}	45	V
Forward current (DC)	I_F	100	mA
Power dissipation	P_D	150	mW
Operating ambient temperature	T_{opr}	– 25 to + 85	°C
Storage temperature	T_{stg}	– 55 to +150	°C

■ Electrical Characteristics (Ta= 25°C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R=40V$			100	nA
Forward voltage (DC)	V_F	$I_F=100mA$		1.05	1.2	V
Diode capacitance	C_D	$V_R=15V, f=1MHz$		0.3	0.5	pF
Forward dynamic resistance	$r_{f1} *$	$I_F=10\mu A, f=100MHz$	1	2		k Ω
	$r_{f2} *$	$I_F=10mA, f=100MHz$		6	10	Ω

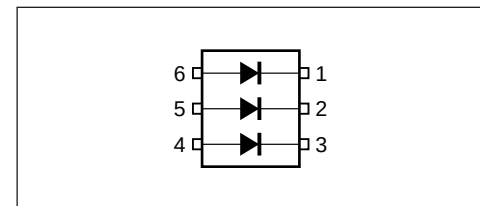
Note 1. Rated input/output frequency : 100MHz
 2. Each characteristic is a standard for each diode
 3. * r_f measurement device : YHP MODEL 4191A RF IMPEDANCE ANALYZER

■ Marking

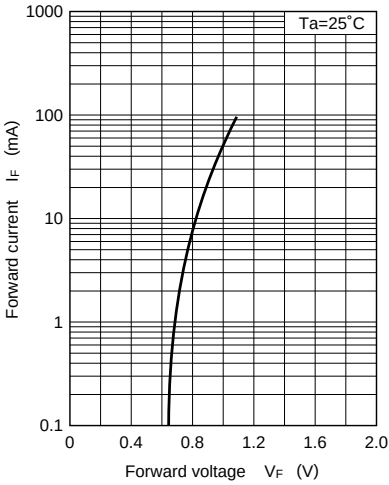


Marking Symbol : M2T

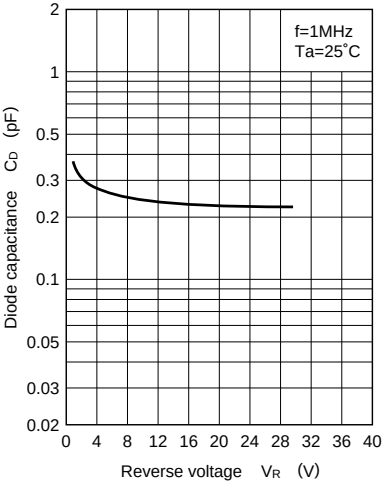
■ Internal Connection



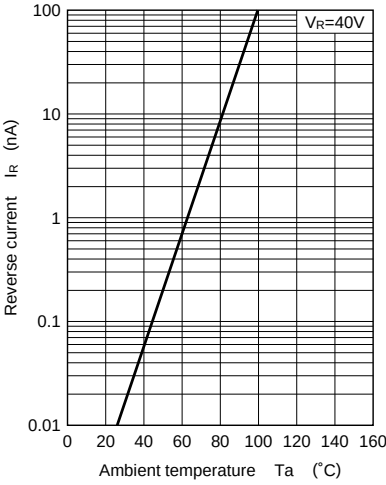
$I_F - V_F$



$C_D - V_R$



$I_R - T_a$



$r_f - I_F$

